

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-61 (Canceled).

62. (Currently Amended) A nitride semiconductor light emitting device comprising;

a substrate,

a first nitride semiconductor layer being undoped and having an impurity concentration less than $1 \times 10^{17}/\text{cm}^3$, said first nitride semiconductor layer being a single layer,

a second nitride semiconductor layer having an n-type electrode and, said second nitride semiconductor layer being a single layer,

a third nitride semiconductor layer being undoped having an impurity concentration less than $1 \times 10^{17}/\text{cm}^3$, said third nitride semiconductor layer and being a super lattice layer of InGaN layers and GaN layers, and

a separate and distinct active layer where electrons and holes are combined.

63. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer is made of GaN or AlGaN and said second nitride semiconductor layer includes Si as an n-type impurity.

64. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said first nitride semiconductor layer is made of GaN or AlGaN.

65. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer has an carrier concentration more than $3 \times 10^{18}/\text{cm}^3$.

66. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer has a resistivity less than $8 \times 10^{-3} \text{ ohm} \cdot \text{cm}$.

67. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

further comprising a buffer layer between said substrate and said first nitride semiconductor layer.

68. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said first nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm .

69. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm ,

70. (Currently Amended) A nitride semiconductor light emitting device comprising:

a substrate,
a first nitride semiconductor layer being undoped having an impurity concentration less than $1 \times 10^{17}/\text{cm}^3$, said first nitride semiconductor layer and being a single layer,

a second nitride semiconductor layer having an n-type electrode, said second nitride semiconductor layer and being a single layer,

a third nitride semiconductor layer being a super lattice layer of GaN layers, and

a separate and distinct active layer where electrons and holes are combined.

71. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer is made of GaN or AlGaN and said second nitride semiconductor layer includes Si as an n-type impurity.

72. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said first nitride semiconductor layer is made of GaN or AlGaN

73. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has an carrier concentration more than $3 \times 10^{18}/\text{cm}^3$.

74. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has a resistivity less than 8×10^{-3} ohm · cm.

75. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

further comprising a buffer layer between said substrate and said first nitride semiconductor layer.

76. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said first nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm ,

77. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm .

78. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said third nitride semiconductor layer being a super lattice layer of undoped GaN layers and Si doped GaN layers.

79. (Previously Presented) The nitride semiconductor light emitting device according to claim 78;

wherein said Si doped GaN layers are doped with Si to $1 \times 10^{19}/\text{cm}^3$.

80. (Previously Presented) The nitride semiconductor light emitting device according to claim 78;

wherein said undoped GaN layers have a thickness of 75 \AA and Si doped GaN layers have a thickness of 25 \AA .

81. (Previously Presented) The nitride semiconductor light emitting device according to claim 78;

wherein said third nitride semiconductor layer has a thickness of 600Å.